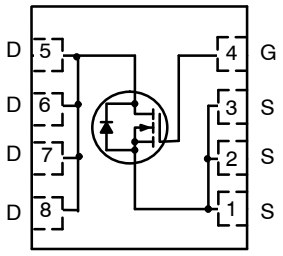
MOSFET – N-Channel, UltraFET Trench

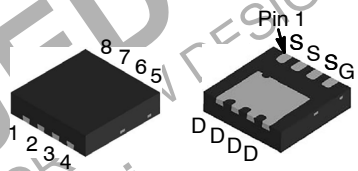
220 V, 7.0 A, 366 mΩ

FDMC2674

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
220 V	366 mΩ @ 10 V	7.0 A



N-CHANNEL MOSFET



WDFN8 3.3 × 3.3, 0.65P
CASE 511DH

General Description

UltraFET device combines characteristics that enable benchmark efficiency in power conversion applications. Optimized for $R_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Features

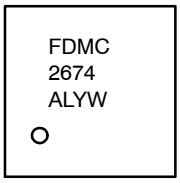
- Max $R_{DS(on)}$ = 366 mΩ at V_{GS} = 10 V, I_D = 1.0 A
- Typ Q_g = 12.7 nC at V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- Optimized Efficiency at High Frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- Pb−Free, Halide Free and RoHS Compliant

Applications

- DC−DC Converters and Off−Line UPS
- Distributed Power Architectures

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi REPRESENTATIVE FOR INFORMATION

MARKING DIAGRAM



FDMC2674 = Specific Device Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	220	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current: Continuous (Silicon limited) T_C = 25°C Continuous (Note 1b) T_A = 25°C Pulsed	 7.0 1.0 13.8	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	11	mJ
P_D	Power Dissipation: T_C = 25°C T_A = 25°C (Note 1a)	 42 2.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

ORDERING INFORMATION

Device	Package	Shipping†
FDMC2674	WDFN8 (Pb−Free, Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

© Semiconductor Components Industries, LLC, 2012

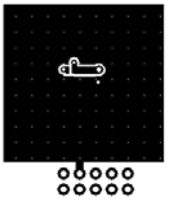
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	220	–	–	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	248	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 176 V, V_{GS} = 0 V	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	3.4	4	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	–10.2	–	mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 1.0 A	–	305	366	mΩ
		V_{GS} = 10 V, I_D = 1.0 A, T_J = 150°C	–	678	814	
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	–	880	1180	pF
C_{oss}	Output Capacitance		–	70	95	pF
C_{rss}	Reverse Transfer Capacitance		–	11	20	pF
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100 V, I_D = 1.0 A, V_{GS} = 10 V, R_{GEN} = 2.4 Ω	–	9	18	ns
t_r	Rise Time		–	13	23	ns
$t_{d(off)}$	Turn-Off Delay Time		–	15	27	ns
t_f	Fall Time		–	21	34	ns
$Q_{g(TOT)}$	Total Gate Charge at 10 V	V_{GS} = 0 V to 10 V, V_{DD} = 15 V, I_D = 1.0 A	–	12.7	18	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 15 V, I_D = 1.0 A	–	3.8	–	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 15 V, I_D = 1.0 A	–	2.9	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.2 A (Note 2)	–	0.8	1.5	V
t_{rr}	Reverse Recovery Time	I_F = 1.0 A, di/dt = 100 A/μs	–	–	60	ns
Q_{rr}	Reverse Recovery Charge		–	–	109	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user’s board design.
   (a) $R_{\theta JA}$ = 60°C/W when mounted on a 1 in^2 pad of 2 oz copper, 1.5’ × 1.5’ × 0.062’ thick PCB.
   (b) $R_{\theta JA}$ = 135°C/W when mounted on a minimum pad of 2 oz copper.



a) 60°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b) 135°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25°C; N-ch: L = 1 mH, I_{AS} = 4.7 A, V_{DD} = 25 V, V_{GS} = 10 V.

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

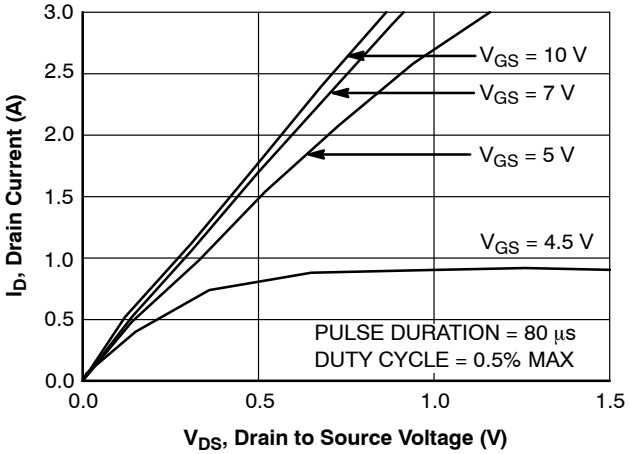


Figure 1. On−Region Characteristics

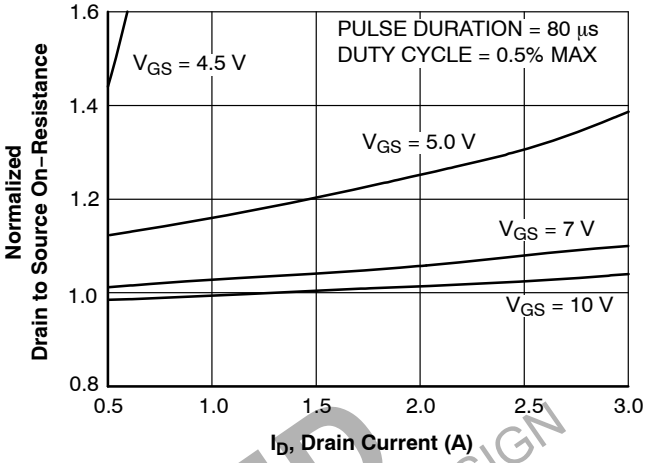


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

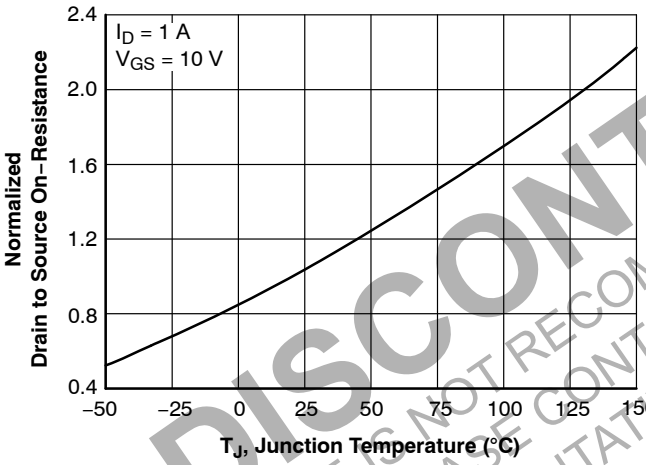


Figure 3. Normalized On−Resistance vs. Junction Temperature

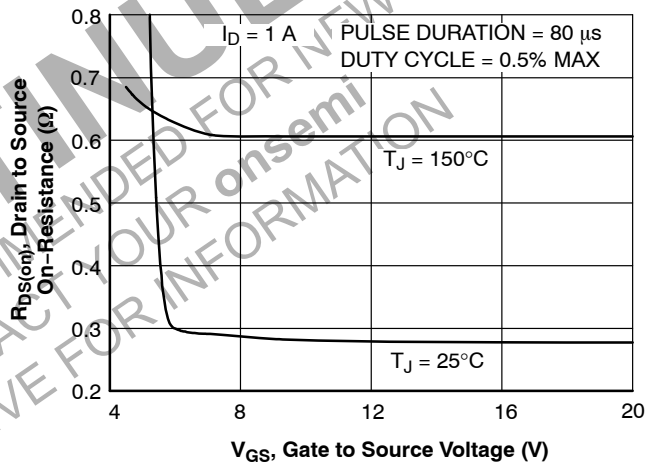


Figure 4. On−Resistance vs. Gate to Source Voltage

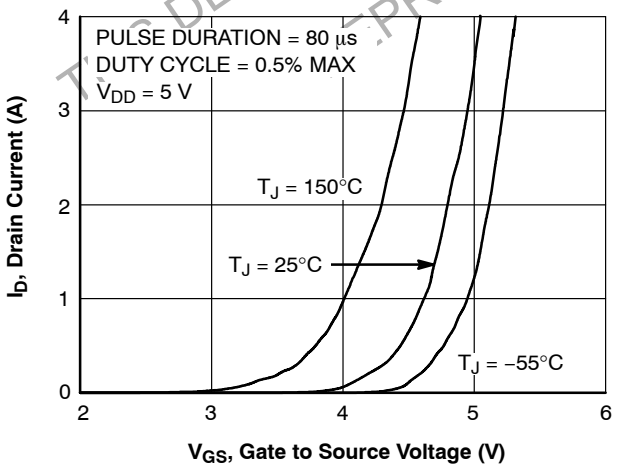


Figure 5. Transfer Characteristics

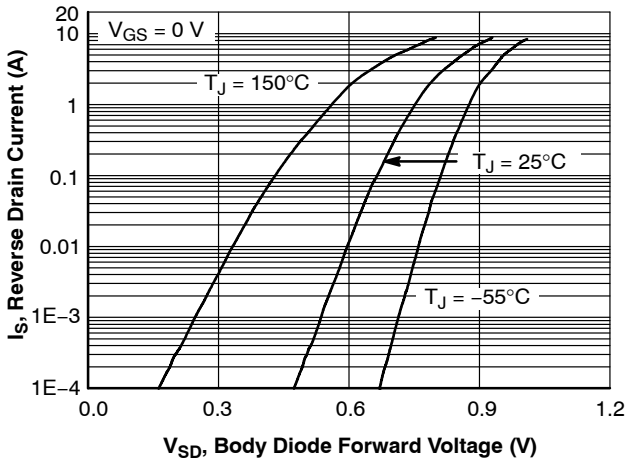


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

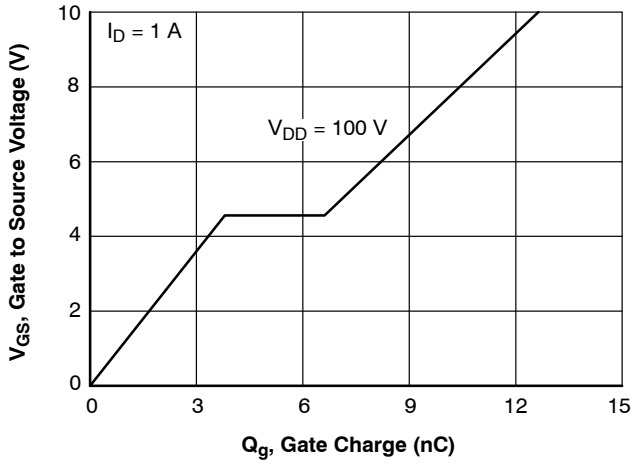


Figure 7. Gate Charge Characteristics

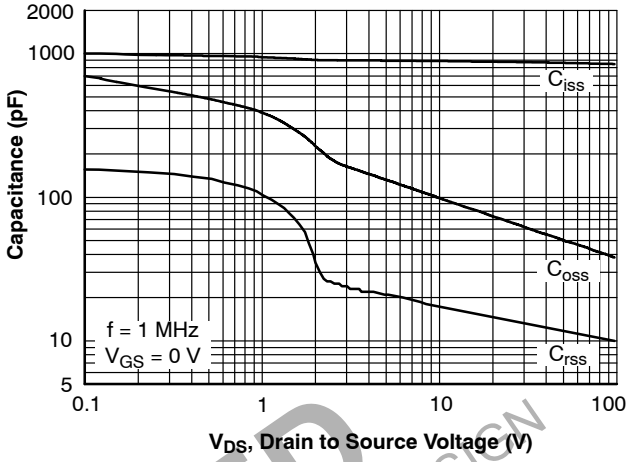


Figure 8. Capacitance vs. Drain to Source Voltage

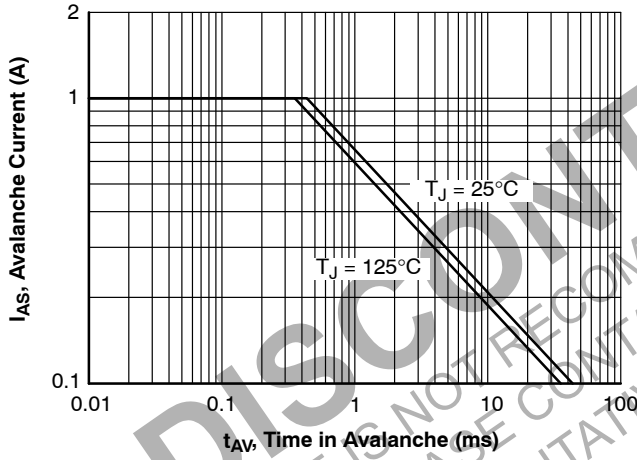


Figure 9. Unclamped Inductive Switching Capability

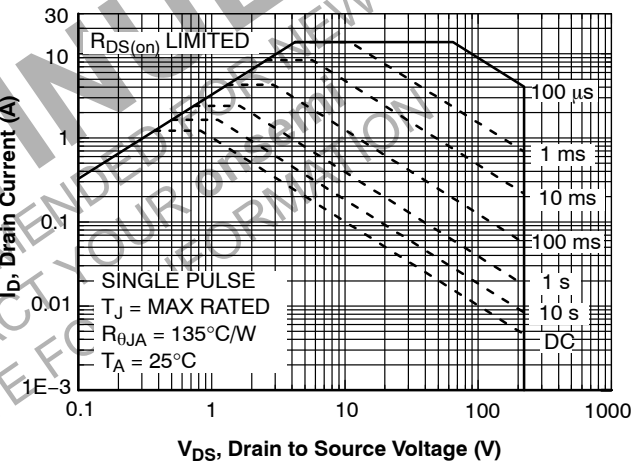


Figure 10. Forward Bias Safe Operating Area

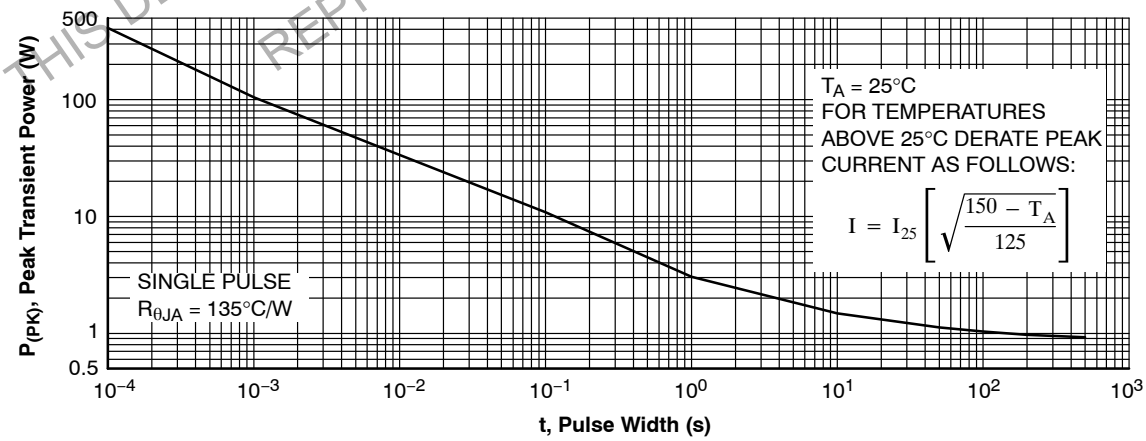


Figure 11. Single Pulse Maximum Power Dissipation

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR ONSEMI
REPRESENTATIVE FOR INFORMATION

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

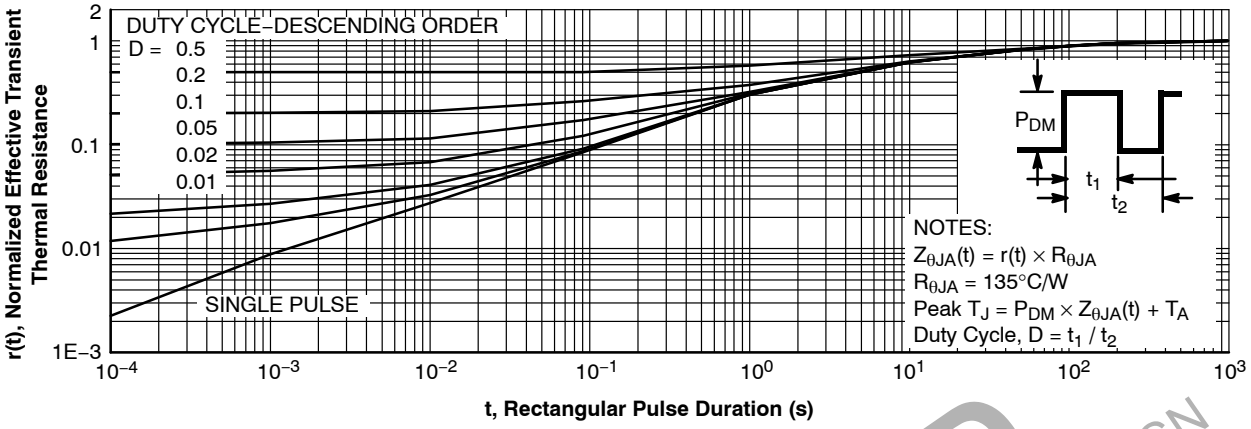
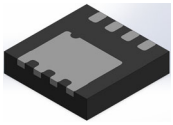


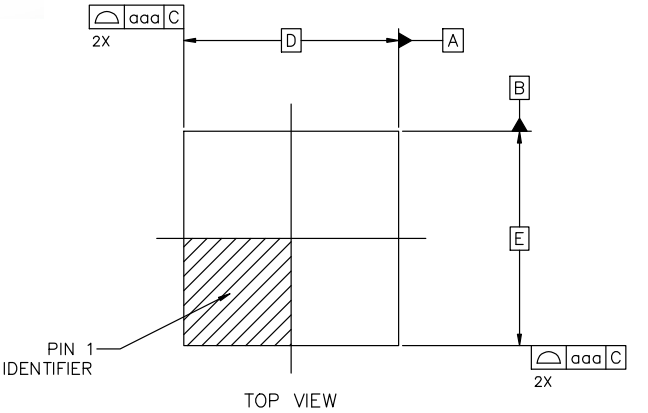
Figure 12. Transient Thermal Response Curve

DISCONTINUED
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION



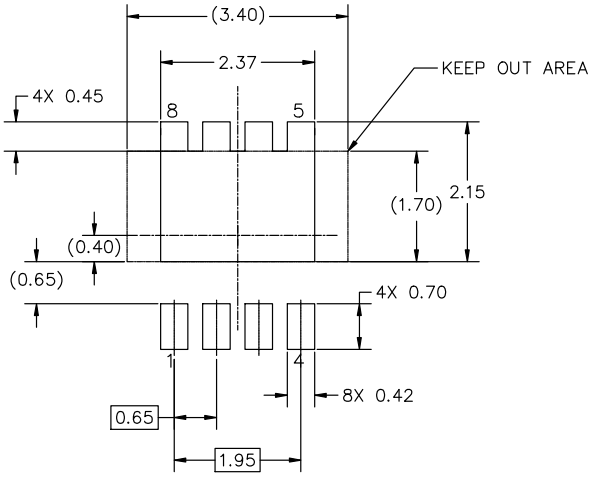
WDFN−8 3.30x3.30x0.75, 0.65P
CASE 511DH
ISSUE A

DATE 04 DEC 2025



NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.025	0.05
A3		0.20 REF	
b	0.30	0.35	0.40
D		3.30 BSC	
D2	2.22	2.27	2.32
E		3.30 BSC	
E2	1.95	2.00	2.05
e		0.65 BSC	
k		0.80 REF	
k1		0.50 REF	
L	0.45	0.50	0.55
L1	0.25	0.30	0.35
TOLERANCE FORM & POSITION			
aaa		0.05	
bbb		0.10	
ccc		0.10	
ddd		0.05	
eee		0.08	



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques reference manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON13625G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**WDFN−8 3.30x3.30x0.75, 0.65P**	**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.